AMENDMENTS TO THE CLAIMS

Please cancel claims 5 and amend claims 1, 21 and 24 as shown below.

1. (Currently Amended) A semiconductor package comprising:

a package support member;

a top package member coupled to said package support member;

a plurality of pins attached to said package support member;

a plurality of package leads in electrical communication with said plurality of pins; and

a radiation power source mounted to said semiconductor package and contained within said top package member, said radiation power source independent and separate from any ICs mounted to said package support member, wherein said radiation power source comprises at least one radioactive source and at least one semiconductor junction producing current in response to radiation emitted by said radioactive source.

2. (Previously Presented) The semiconductor package of claim 1, further comprising an IC mounted to said package support member and in electrical communication with said plurality of package leads.

3. (Withdrawn) The semiconductor package of claim 1, wherein said radiation power source is mounted on said package support member.

4. (Withdrawn) The semiconductor package of claim 1, further comprising a top package member coupled to said package support member, wherein said radiation power source is mounted to said top package member.

5. (Canceled)

6. (Original) The semiconductor package of claim 1, wherein said semiconductor package is selected from the group consisting of DIPs, PQFPs, SIPs, ceramic flatpacks, PIN packages, SOIC packages, QSOPs, LCC packages, and PLCCs.

7. (Original) The semiconductor package of claim 2, wherein said IC is a MEMs device.

8. (Withdrawn) The semiconductor package of claim 2, wherein said radiation power source is electrically coupled to said IC via a pair of package substrate leads.

9. (Original) The semiconductor package of claim 1, further comprising at least a pair of power source leads in electrical communication with at least a pair of corresponding IC package leads.

10. (Withdrawn) The semiconductor package of claim 1, further comprising at least a pair of power source leads in electrical communication with at least a pair of said plurality of pins attached to said package support member.

11. (Previously Presented) The semiconductor package of claim 1, wherein said radiation power source is a beta cell.

12. (Original) The semiconductor package of claim 11, wherein said beta cell is comprised of an icosahedral boride semiconductor.

13. (Previously Presented) The semiconductor package of claim 1, wherein said at least one semiconductor junction is comprised of a homo-junction.

14. (Previously Presented) The semiconductor package of claim 1, wherein said at least one semiconductor junction is comprised of a hetero-junction.

15. (Withdrawn) The semiconductor package of claim 1, wherein said radiation power source is mounted to said semiconductor package via eutectics.

16. (Withdrawn) The semiconductor package of claim 1, wherein said radiation power source is mounted to said semiconductor package via epoxies.

17. (Withdrawn) The semiconductor package of claim 1, wherein said radiation power source is mounted to said semiconductor package via glass frit materials.

18. (Original) The semiconductor package of claim 1, further comprising radiation shielding.

19. (Previously Presented) The semiconductor package of claim 18, wherein said radiation shielding at least partially encompasses said radiation power source.

20. (Previously Presented) The semiconductor package of claim 4, wherein said top package member is hermetically sealed to said package support member.

21. (Currently Amended) The semiconductor package of claim 1 ~~5~~, wherein said top package member is hermetically sealed to said package support member.

22. (Previously Presented) The semiconductor package of claim 1, wherein said package support member is fabricated from a ceramic, a plastic or a PCB.

23. (Withdrawn) The semiconductor package of claim 1, wherein said radiation power source is connected to a portion of said plurality of package leads via wire interconnects.

24. (Withdrawn) A semiconductor package comprising:

a package support member;

an IC die support member mounted to said package support member;

an IC mounted to said IC die support member, said IC having a plurality of contact pads;

a plurality of package leads on said package support member;

a plurality of wire interconnects in electrical communication with said plurality of contact pads and said plurality of package leads;

a plurality of pins in electrical communication with said plurality of package leads;

a package lid attached to said package support member; and

a radiation power source contained within ~~mounted to~~ said package lid, said radiation power source independent and separate from any ICs mounted to said IC die support member, wherein said radiation power source comprises at least one radioactive source and at least one semiconductor junction producing current in response to radiation emitted by said radioactive source.

25. (Withdrawn) The semiconductor package of claim 24, wherein said radiation power source is electrically coupled to at least a pair of said plurality of contact pads.

26. (Withdrawn) The semiconductor package of claim 24, wherein said radiation power source is electrically coupled to at least a pair of said plurality of pins.

27. (Canceled)

28. (Withdrawn) The semiconductor package of claim 24, wherein said semiconductor package is selected from the group consisting of DIPs, PQFPs, SIPs, ceramic flatpacks, PIN packages, SOIC packages, QSOPs, LCC packages, and PLCCs.

29. (Withdrawn) The semiconductor package of claim 24, wherein said radiation power source is a beta cell.

30. (Withdrawn) The semiconductor package of claim 29, wherein said beta cell is comprised of an icosahedral boride semiconductor.

31. (Withdrawn) The semiconductor package of claim 24, wherein said at least one semiconductor junction is comprised of a homo-junction.

32. (Withdrawn) The semiconductor package of claim 24, wherein said at least one semiconductor junction is comprised of a hetero-junction.